New Product



VS-12EWH06FN-M3

Vishay Semiconductors

Hyperfast Rectifier, 12 A FRED Pt[®]



D-PAK (TO-252AA)

Revision: 06-Apr-11

PRODUCT SUMMARY					
Package	D-PAK (TO-252AA)				
I _{F(AV)}	12 A				
V _R	600 V				
V _F at I _F	2.5 V				
t _{rr} (typ.)	18 ns				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Hyperfast recovery time, reduced Qrr and soft recovery
- 175 °C maximum operating junction temperature
- For PFC CRM/CCM operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V _{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 132 °C	12		
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$	110	А	
Peak repetitive forward current	I _{FM}	$T_{C} = 132 \text{ °C}, f = 20 \text{ kHz}, d = 50 \%$	24		
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
Forward voltage	VF	I _F = 12 A	-	1.73	2.5	V
Torward voltage	۷F	I _F = 12 A, T _J = 125 °C	-	1.34	1.8	
	1	$V_{R} = V_{R}$ rated	-	-	10	
Reverse leakage current I _R		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	100	μA
Junction capacitance	CT	V _R = 600 V	-	8	-	pF
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8	-	nH

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e RoHS

COMPLIANT HALOGEN FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, dI_F/dt = 10$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		18	22	
Reverse recovery time t _{rr}	+	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		-	22	-	
	۲r	T _J = 25 °C	I _F = 12 A dI _F /dt = 200 A/μs V _R = 390 V	-	26	-	A nC
		T _J = 125 °C		-	47	-	
Peak recovery current I _{RRM}		T _J = 25 °C		-	3.5	-	
	IRRM	T _J = 125 °C		-	5.4	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	48	-	
		T _J = 125 °C		-	137	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.3	1.7	°C/W
Approximate weight				0.3		g
Approximate weight				0.01		oz.
Marking device		Case style D-PAK (TO-252AA)		12EW	H06FN	

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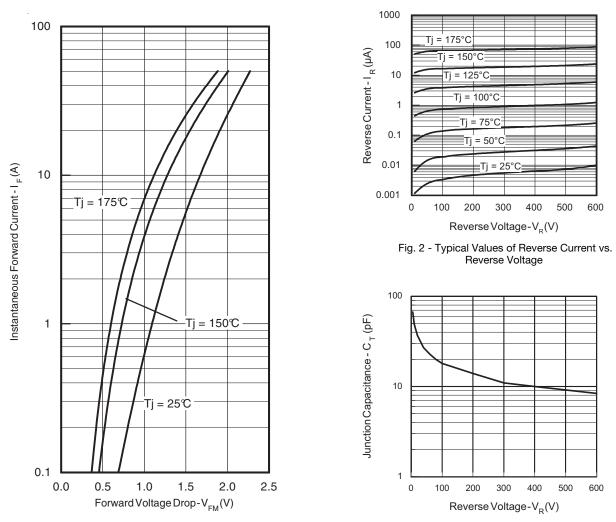
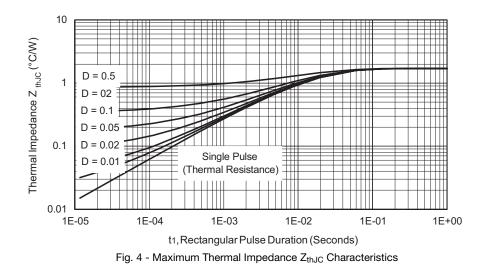


Fig. 1 - Typical Forward Voltage Drop Characteristics

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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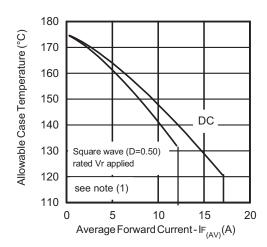


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

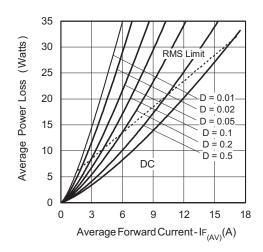


Fig. 6 - Forward Power Loss Characteristics

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

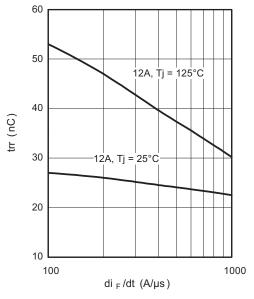


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

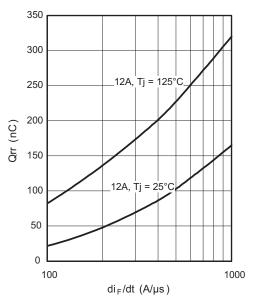


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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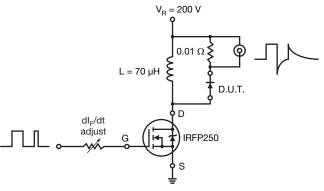
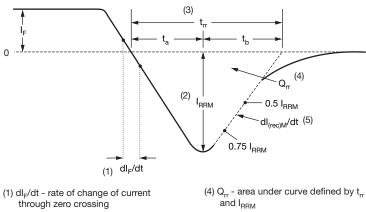
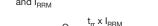


Fig. 9 - Reverse Recovery Parameter Test Circuit



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



$$Q_{rr} = \frac{11}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 12 A FRED Pt®



ORDERING INFORMATION TABLE

Device code	VS-	12	Е	w	н	06	FN	TRL	-M3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)
	 1 - Vishay Semiconductors product 2 - Current rating (12 = 12 A) 3 - Circuit configuration: 								
	4	E = Pac	Single o kage ide	diode entifier:					
	5	- H=		ast recov	-				
	6 · 7 ·		tage rati = TO-25	ng (06 = 52AA	= 600 V)				
	8		one = Ti R = Tap	ube e and re	el				
				pe and i		oriente	d)		
	9.			pe and ntal digit		ht orien	ted)		
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-M3 = Halogen-free, RoHS compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-12EWH06FN-M3	75	3000	Antistatic plastic tube				
VS-12EWH06FNTR-M3	2000	2000	13" diameter reel				
VS-12EWH06FNTRL-M3	3000	3000	13" diameter reel				
VS-12EWH06FNTRR-M3	3000	3000	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95016					
Part marking information	www.vishay.com/doc?95176				
Packaging information	www.vishay.com/doc?95033				
SPICE model	www.vishay.com/doc?95220				

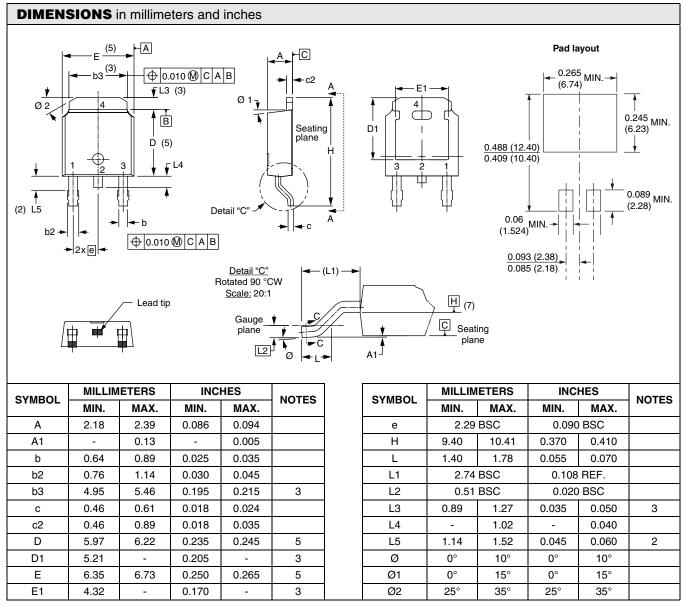
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Vishay High Power Products

D-PAK (TO-252AA)



Notes

- $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension uncontrolled in L5
- ⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- ⁽⁵⁾ Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁶⁾ Dimension b1 and c1 applied to base metal only
- ⁽⁷⁾ Datum A and B to be determined at datum plane H
- ⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA



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